



*IFW/Receipt*

DOCKET NO.: 252311US2S/sma

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

IN RE APPLICATION OF:

GROUP: 2811

Syotaro ONO, et al.

SERIAL NO: 10/829,173

ATTENTION:

FILING RECEIPT CORRECTIONS

FILED: April 22, 2004

FOR: SEMICONDUCTOR DEVICE HAVING VERTICAL MOS GATE  
STRUCTURE AND METHOD OF MANUFACTURING THE SAME

**REQUEST FOR CORRECTED OFFICIAL FILING RECEIPT**

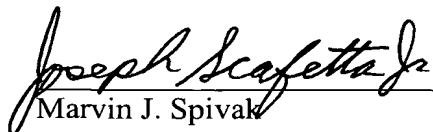
Office of Initial Patent Examination  
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Sir:

The Patent Office is requested to provide a corrected Official Filing Receipt for the attached. No fees are required. If you have any questions, please do not hesitate to contact us.

Respectfully Submitted,

OBLON, SPIVAK, McCLELLAND,  
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(OSMMN 05/04)



## UNITED STATES PATENT AND TRADEMARK OFFICE

NOV 23 2004

UNITED STATES DEPARTMENT OF COMMERCE  
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APPL NO.	FILING OR 371 (c) DATE	ART UNIT	FIL FEE REC'D	ATTY. DOCKET NO	DRAWINGS	TOT CLMS	IND CLMS
10/829,173	04/22/2004	2811	900	252311US2S	4	18	3

22850  
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ALEXANDRIA, VA 22314

CONFIRMATION NO. 6045  
UPDATED FILING RECEIPT



\*OC000000013927555\*

Date Mailed: 09/29/2004

Receipt is acknowledged of this regular Patent Application. It will be considered in its order and you will be notified as to the results of the examination. Be sure to provide the U.S. APPLICATION NUMBER, FILING DATE, NAME OF APPLICANT, and TITLE OF INVENTION when inquiring about this application. Fees transmitted by check or draft are subject to collection. Please verify the accuracy of the data presented on this receipt. If an error is noted on this Filing Receipt, please write to the Office of Initial Patent Examination's Filing Receipt Corrections, facsimile number 703-746-9195. Please provide a copy of this Filing Receipt with the changes noted thereon. If you received a "Notice to File Missing Parts" for this application, please submit any corrections to this Filing Receipt with your reply to the Notice. When the USPTO processes the reply to the Notice, the USPTO will generate another Filing Receipt incorporating the requested corrections (if appropriate).

## Applicant(s)

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Power of Attorney: The patent practitioners associated with Customer Number 22850.

Domestic Priority data as claimed by applicant

## Foreign Applications

JAPAN 2003-118462 04/23/2003

If Required, Foreign Filing License Granted: 07/07/2004

The number of your priority application, to be used for filing abroad under the Paris Convention is,  
**US10/829,173**

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Early Publication Request: No

RECEIVED: 9129104

OBLON, SPIVAK, McCLELLAND  
MAIER & NEUSTADT, P.C.

DOCKETING DEPT.

Initials/Date Docketed: PP 9129104

Type of Resp(s): \_\_\_\_\_

Due Date(s): \_\_\_\_\_

## Title

Semiconductor device having verical MOS gate structure and method of manufacturing the same

## Preliminary Class

257

PLEASE NOTE THAT THE TITLE IS INCORECT. IT SHOULD READ AS FOLLOWS:

SEMICONDUCTOR DEVICE HAVING VERTICAL MOS GATE STRUCTURE AND  
METHOD OF MANUFACTURING THE SAME